

## SN74LVC1G08-Q1 Single 2-input positive-AND gate

### 1 Features

- AEC-Q100 Qualified for Automotive Applications:
  - Device Temperature Grade 1:  $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ ,  $T_A$
- Supports 5-V  $V_{CC}$  Operation
- Over-voltage Tolerant Inputs Accept Voltages to 5.5 V
- Provides Down Translation to  $V_{CC}$
- Low Power Consumption, 10- $\mu\text{A}$  Max  $I_{CC}$
- $\pm 24\text{-mA}$  Output Drive at 3.3 V
- $I_{off}$  Supports Live Insertion, Partial-Power-Down Mode, and Back Drive Protection
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
  - 2000-V Human-Body Model (A114-A)
  - 200-V Machine Model (A115-A)
  - 1000-V Charged-Device Model (C101)

### 2 Applications

- Fully qualified for automotive applications
- Combine power good signals for multiple power rails
- Prevent a signal from being passed until a condition is true
- Combine active-low error signals

### 3 Description

This single 2-input positive-AND gate is designed for 1.65-V to 5.5-V  $V_{CC}$  operation.

The SN74LVC1G08-Q1 device performs the Boolean function or  $Y = A \cdot B$  or  $Y = \overline{A + B}$  in positive logic.

This device is fully specified for partial-power-down applications using I off. The I off circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

The CMOS device has high output drive while maintaining low static power dissipation over a broad  $V_{CC}$  operating range.

The SN74LVC1G08 is available in a variety of packages, including the small DRY package with a body size of 1.45 mm  $\times$  1.00 mm.

#### Device Information<sup>(1)</sup>

DEVICE NAME	PACKAGE	BODY SIZE
SN74LVC1G08Q	SOT-23 (5)	2.90mm $\times$ 1.60mm
	SC70 (5)	2.00mm $\times$ 1.25mm
	SON (6)	1.45mm $\times$ 1.00mm

(1) For all available packages, see the orderable addendum at the end of the datasheet.



## Table of Contents

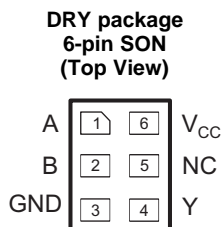
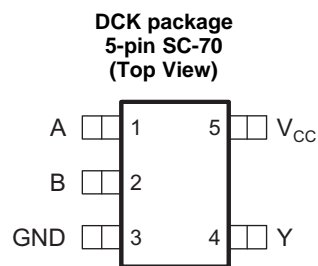
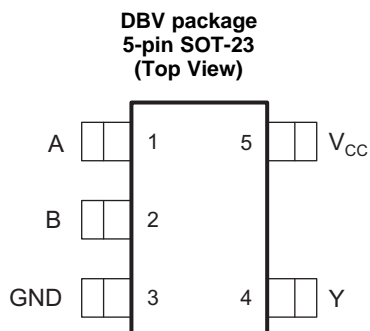
<b>1 Features</b> .....	<b>1</b>	8.1 Overview .....	10
<b>2 Applications</b> .....	<b>1</b>	8.2 Functional Block Diagram .....	10
<b>3 Description</b> .....	<b>1</b>	8.3 Feature Description .....	10
<b>4 Revision History</b> .....	<b>2</b>	8.4 Device Functional Modes .....	10
<b>5 Pin Configuration and Functions</b> .....	<b>3</b>	<b>9 Application and Implementation</b> .....	<b>11</b>
<b>6 Specifications</b> .....	<b>4</b>	9.1 Application Information .....	11
6.1 Absolute Maximum Ratings .....	4	9.2 Typical Application .....	11
6.2 ESD Ratings .....	4	<b>10 Power Supply Recommendations</b> .....	<b>12</b>
6.3 Recommended Operating Conditions .....	5	<b>11 Layout</b> .....	<b>12</b>
6.4 Thermal Information .....	5	11.1 Layout Guidelines .....	12
6.5 Electrical Characteristics .....	6	11.2 Layout Example .....	12
6.6 Switching Characteristics, $T_A = -40^{\circ}\text{C}$ to $125^{\circ}\text{C}$ .....	6	<b>12 Device and Documentation Support</b> .....	<b>13</b>
6.7 Switching Characteristics, $T_A = -40^{\circ}\text{C}$ to $85^{\circ}\text{C}$ .....	6	12.1 Trademarks .....	13
6.8 Operating Characteristics .....	6	12.2 Electrostatic Discharge Caution .....	13
6.9 Typical Characteristics .....	7	12.3 Glossary .....	13
<b>7 Parameter Measurement Information</b> .....	<b>8</b>	<b>13 Mechanical, Packaging, and Orderable Information</b> .....	<b>13</b>
<b>8 Detailed Description</b> .....	<b>10</b>		

## 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

<b>Changes from Revision F (April 2008) to Revision G</b>	<b>Page</b>
• Changed data sheet to new TI format .....	1
• Added DRY package to <i>Device Information</i> table .....	1
• Added <i>Thermal Information</i> table .....	5
• Added <i>Typical Characteristics</i> .....	7
• Added <i>Detailed Description</i> section .....	10
• Added <i>Application and Implementation</i> section .....	11
• Added <i>Power Supply Recommendations</i> section .....	12
• Added <i>Layout</i> section .....	12

## 5 Pin Configuration and Functions



NC – No internal connection

See mechanical drawings for dimensions.

### Pin Functions

NAME	PIN		I/O	DESCRIPTION
	NO. DBV, DCK	NO. DRY		
A	1	1	Input	Input A
B	2	2	Input	Input B
GND	3	3	—	Ground
Y	4	4	Output	Output Y
V <sub>CC</sub>	5	6	—	Positive Supply
NC		5	—	No internal connection

## 6 Specifications

### 6.1 Absolute Maximum Ratings<sup>(1)</sup>

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
$V_{CC}$	Supply voltage range	-0.5	6.5	V
$V_I$	Input voltage range <sup>(2)</sup>	-0.5	6.5	V
$V_O$	Voltage range applied to any output in the high-impedance or power-off state <sup>(2)</sup>	-0.5	6.5	V
$V_O$	Voltage range applied to any output in the high or low state <sup>(2)(3)</sup>	-0.5	$V_{CC} + 0.5$	V
$I_{IK}$	Input clamp current	$V_I < 0$	-50	mA
$I_{OK}$	Output clamp current	$V_O < 0$	-50	mA
$I_O$	Continuous output current		±50	mA
	Continuous current through $V_{CC}$ or GND		±100	mA
$T_J$	Junction temperature		150	°C
$T_{stg}$	Storage temperature	-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) The value of  $V_{CC}$  is provided in the *Recommended Operating Conditions* table.

### 6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per AEC Q100-002 <sup>(1)</sup> HBM ESD Classification Level	±2000	V
		Charged-device model (CDM), per AEC Q100-011 CDM ESD Classification Level	±1000	

- (1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

### 6.3 Recommended Operating Conditions<sup>(1)</sup>

		MIN	MAX	UNIT	
V <sub>CC</sub>	Supply voltage	Operating	1.65	5.5	V
		Data retention only	1.5		
V <sub>IH</sub>	High-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	0.65 × V <sub>CC</sub>		V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.7		
		V <sub>CC</sub> = 3 V to 3.6 V	2		
		V <sub>CC</sub> = 4.5 V to 5.5 V	0.7 × V <sub>CC</sub>		
V <sub>IL</sub>	Low-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V		0.35 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 2.3 V to 2.7 V		0.7	
		V <sub>CC</sub> = 3 V to 3.6 V		0.8	
		V <sub>CC</sub> = 4.5 V to 5.5 V		0.3 × V <sub>CC</sub>	
V <sub>I</sub>	Input voltage	0	5.5	V	
V <sub>O</sub>	Output voltage	0	V <sub>CC</sub>	V	
I <sub>OH</sub>	High-level output current	V <sub>CC</sub> = 1.65 V		–4	mA
		V <sub>CC</sub> = 2.3 V		–8	
		V <sub>CC</sub> = 3 V		–16	
		V <sub>CC</sub> = 4.5 V		–24	
I <sub>OL</sub>	Low-level output current	V <sub>CC</sub> = 1.65 V		4	mA
		V <sub>CC</sub> = 2.3 V		8	
		V <sub>CC</sub> = 3 V		16	
		V <sub>CC</sub> = 4.5 V		24	
Δt/Δv	Input transition rise or fall rate	V <sub>CC</sub> = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V		20	ns/V
		V <sub>CC</sub> = 3.3 V ± 0.3 V		10	
		V <sub>CC</sub> = 5 V ± 0.5 V		5	
T <sub>A</sub>	Operating free-air temperature	Q-suffix devices	–40	125	°C
		I-suffix devices	–40	85	°C

(1) All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number [SCBA004](#).

### 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>	SN74LVC1G08-Q1			UNIT	
	DBV	DCK	DRY		
	5 PINS	5 PINS	6 PINS		
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	209.4	244.2	264.4	°C/W
R <sub>θJctop</sub>	Junction-to-case (top) thermal resistance	132.5	156.1	166.6	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	118.1	130.8	142.2	°C/W
Ψ <sub>JT</sub>	Junction-to-top characterization parameter	48.8	47.2	26.1	°C/W
Ψ <sub>JB</sub>	Junction-to-board characterization parameter	117.4	130.0	141.6	°C/W
R <sub>θJcbot</sub>	Junction-to-case (bottom) thermal resistance	–	–	–	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC package thermal metrics application report](#).

## 6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V <sub>CC</sub>	–40°C to 85°C			–40°C to 125°C RECOMMENDED			UNIT
			MIN	TYP <sup>(1)</sup>	MAX	MIN	TYP	MAX	
V <sub>OH</sub>	I <sub>OH</sub> = –100 μA	1.65 V to 5.5 V	V <sub>CC</sub> – 0.1			V <sub>CC</sub> – 0.15			V
	I <sub>OH</sub> = –4 mA	1.65 V	1.2			1.2			
	I <sub>OH</sub> = –8 mA	2.3 V	1.9			1.9			
	I <sub>OH</sub> = –16 mA	3 V	2.4			2.4			
	I <sub>OH</sub> = –24 mA		2.3			2.3			
	I <sub>OH</sub> = –32 mA	4.5 V	3.8			3.8			
V <sub>OL</sub>	I <sub>OL</sub> = 100 μA	1.65 V to 5.5 V	0.1			0.1			V
	I <sub>OL</sub> = 4 mA	1.65 V	0.45			0.45			
	I <sub>OL</sub> = 8 mA	2.3 V	0.3			0.3			
	I <sub>OL</sub> = 16 mA	3 V	0.4			0.4			
	I <sub>OL</sub> = 24 mA		0.55			0.55			
	I <sub>OL</sub> = 32 mA	4.5 V	0.55			0.55			
I <sub>I</sub>	A or B inputs	V <sub>I</sub> = 5.5 V or GND	0 to 5.5 V			±5			μA
I <sub>off</sub>		V <sub>I</sub> or V <sub>O</sub> = 5.5 V	0			±10			μA
I <sub>CC</sub>		V <sub>I</sub> = 5.5 V or GND, I <sub>O</sub> = 0	1.65 V to 5.5 V			10			μA
ΔI <sub>CC</sub>		One input at V <sub>CC</sub> – 0.6 V, Other inputs at V <sub>CC</sub> or GND	3 V to 5.5 V			500			μA
C <sub>i</sub>		V <sub>I</sub> = V <sub>CC</sub> or GND	3.3 V			4			pF

 (1) All typical values are at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> = 25°C.

## 6.6 Switching Characteristics, T<sub>A</sub> = –40°C to 125°C

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	–40°C to 125°C								UNIT
			V <sub>CC</sub> = 1.8 V ± 0.15 V		V <sub>CC</sub> = 2.5 V ± 0.2 V		V <sub>CC</sub> = 3.3 V ± 0.3 V		V <sub>CC</sub> = 5 V ± 0.5 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t <sub>pd</sub>	A or B	Y	1	10	1	7.5	1	6.5	1	6	ns

## 6.7 Switching Characteristics, T<sub>A</sub> = –40°C to 85°C

over recommended operating free-air temperature range, (unless otherwise noted) (see Figure 4)

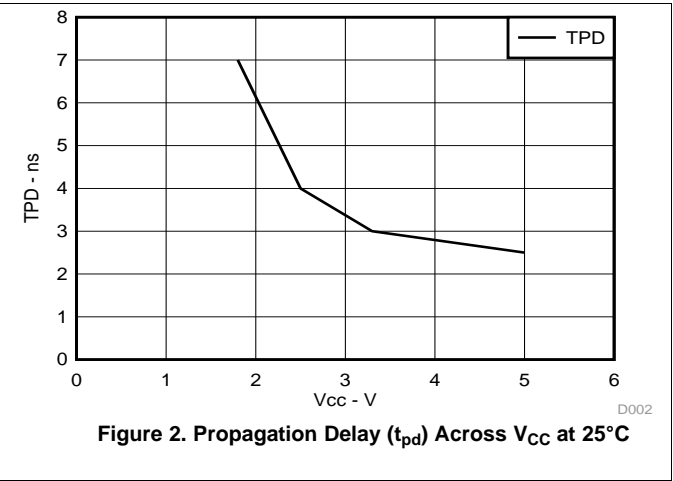
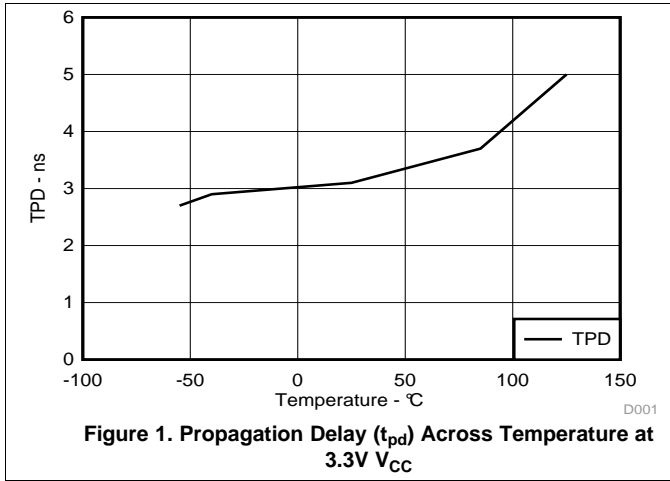
PARAMETER	FROM (INPUT)	TO (OUTPUT)	–40°C to 85°C								UNIT
			V <sub>CC</sub> = 1.8 V ± 0.15 V		V <sub>CC</sub> = 2.5 V ± 0.2 V		V <sub>CC</sub> = 3.3 V ± 0.3 V		V <sub>CC</sub> = 5 V ± 0.5 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t <sub>pd</sub>	A or B	Y	2.4	8	1.1	5.5	1	4.5	1	4	ns

## 6.8 Operating Characteristics

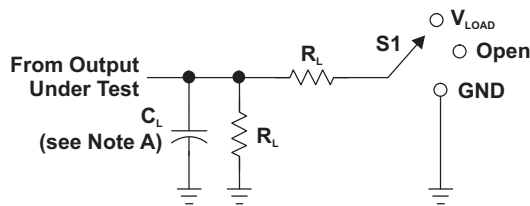
 T<sub>A</sub> = 25°C

PARAMETER	TEST CONDITIONS	V <sub>CC</sub> = 1.8 V	V <sub>CC</sub> = 2.5 V	V <sub>CC</sub> = 3.3 V	V <sub>CC</sub> = 5 V	UNIT	
		TYP	TYP	TYP	TYP		
C <sub>pd</sub>	Power dissipation capacitance	f = 10 MHz	21	24	26	31	pF

### 6.9 Typical Characteristics



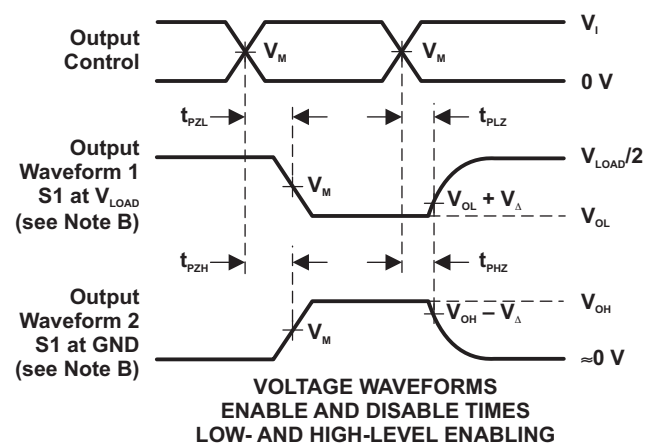
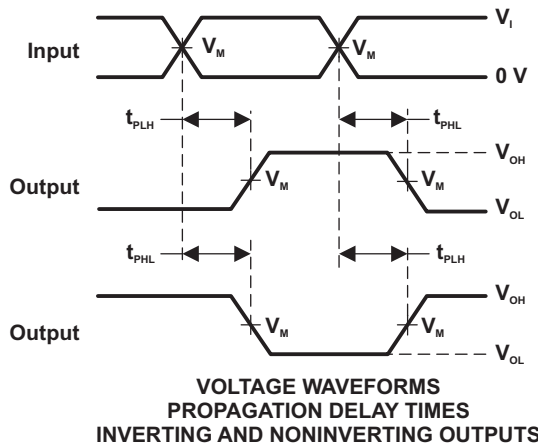
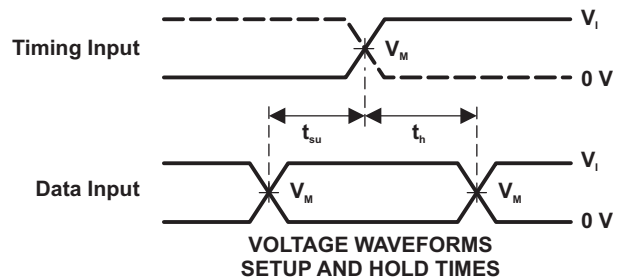
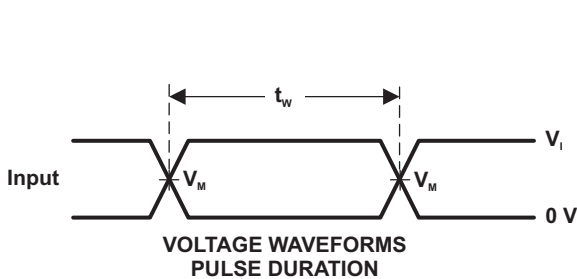
## 7 Parameter Measurement Information



LOAD CIRCUIT

TEST	S1
$t_{PLH}/t_{PHL}$	Open
$t_{PLZ}/t_{PZL}$	$V_{LOAD}$
$t_{PHZ}/t_{PZH}$	GND

$V_{CC}$	INPUTS		$V_M$	$V_{LOAD}$	$C_L$	$R_L$	$V_{\Delta}$
	$V_i$	$t_i/t_r$					
$1.8\text{ V} \pm 0.15\text{ V}$	$V_{CC}$	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	1 M $\Omega$	0.15 V
$2.5\text{ V} \pm 0.2\text{ V}$	$V_{CC}$	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	1 M $\Omega$	0.15 V
$3.3\text{ V} \pm 0.3\text{ V}$	3 V	$\leq 2.5\text{ ns}$	1.5 V	6 V	15 pF	1 M $\Omega$	0.3 V
$5\text{ V} \pm 0.5\text{ V}$	$V_{CC}$	$\leq 2.5\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	1 M $\Omega$	0.3 V

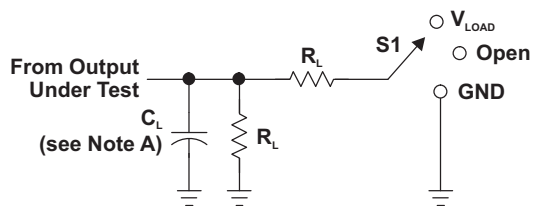


- NOTES:
- A.  $C_L$  includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
  - C. All input pulses are supplied by generators having the following characteristics:  $PRR \leq 10\text{ MHz}$ ,  $Z_o = 50\ \Omega$ .
  - D. The outputs are measured one at a time, with one transition per measurement.
  - E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
  - F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
  - G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .
  - H. All parameters and waveforms are not applicable to all devices.

Figure 3. Load Circuit and Voltage Waveforms



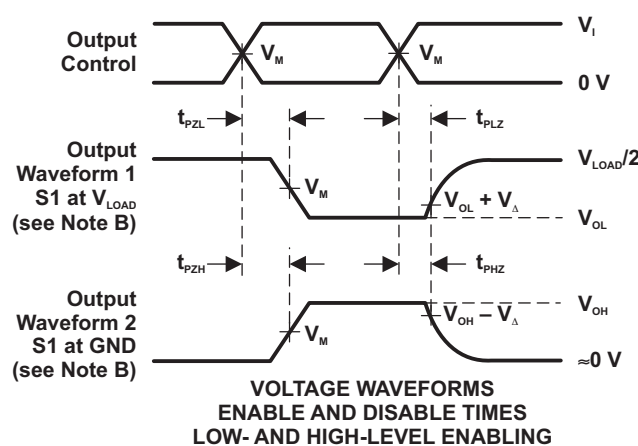
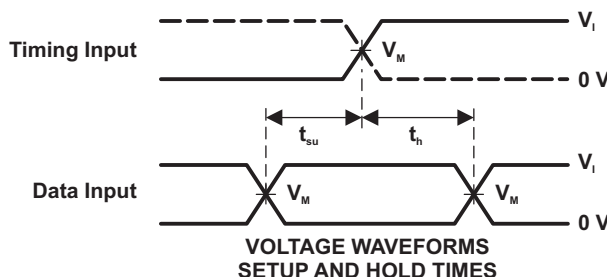
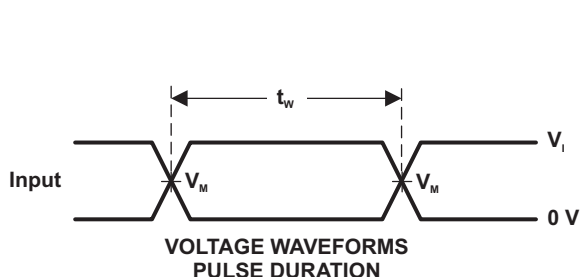
Parameter Measurement Information (continued)



LOAD CIRCUIT

TEST	S1
$t_{PLH}/t_{PHL}$	Open
$t_{PLZ}/t_{PZL}$	$V_{LOAD}$
$t_{PHZ}/t_{PZH}$	GND

$V_{CC}$	INPUTS		$V_M$	$V_{LOAD}$	$C_L$	$R_L$	$V_{\Delta}$
	$V_I$	$t_r/t_f$					
$1.8\text{ V} \pm 0.15\text{ V}$	$V_{CC}$	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	1 k $\Omega$	0.15 V
$2.5\text{ V} \pm 0.2\text{ V}$	$V_{CC}$	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	500 $\Omega$	0.15 V
$3.3\text{ V} \pm 0.3\text{ V}$	3 V	$\leq 2.5\text{ ns}$	1.5 V	6 V	50 pF	500 $\Omega$	0.3 V
$5\text{ V} \pm 0.5\text{ V}$	$V_{CC}$	$\leq 2.5\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	50 pF	500 $\Omega$	0.3 V



- NOTES: A.  $C_L$  includes probe and jig capacitance.  
 B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.  
 C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_o = 50\ \Omega$ .  
 D. The outputs are measured one at a time, with one transition per measurement.  
 E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .  
 F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{on}$ .  
 G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .  
 H. All parameters and waveforms are not applicable to all devices.

Figure 4. Load Circuit and Voltage Waveforms

## 8 Detailed Description

### 8.1 Overview

The SN74LVC1G08Q device contains one 2-input positive AND gate device and performs the Boolean function  $Y = A \cdot B$  or  $Y = \overline{\overline{A} + \overline{B}}$ . This device is fully specified for partial-power-down applications using Ioff. The Ioff circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

### 8.2 Functional Block Diagram

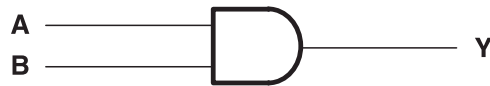


Figure 5. Positive Logic

### 8.3 Feature Description

- Wide operating voltage range.
  - Operates from 1.65 V to 5.5 V.
- Allows down voltage translation.
- Inputs accept voltages to 5.5 V.
- I<sub>off</sub> feature allows voltages on the inputs and outputs when V<sub>CC</sub> is 0 V.

### 8.4 Device Functional Modes

Table 1. Function Table

INPUTS		OUTPUT Y
A	B	
H	H	H
L	X	L
X	L	L

## 9 Application and Implementation

### 9.1 Application Information

The SN74LVC1G08Q is a high-drive CMOS device that can be used for implementing AND logic with a high output drive, such as an LED application. It can produce 24 mA of drive current at 3.3 V making it ideal for driving multiple outputs and good for high speed applications up to 100 MHz. The inputs are 5.5 V tolerant allowing it to translate down to  $V_{CC}$ .

### 9.2 Typical Application

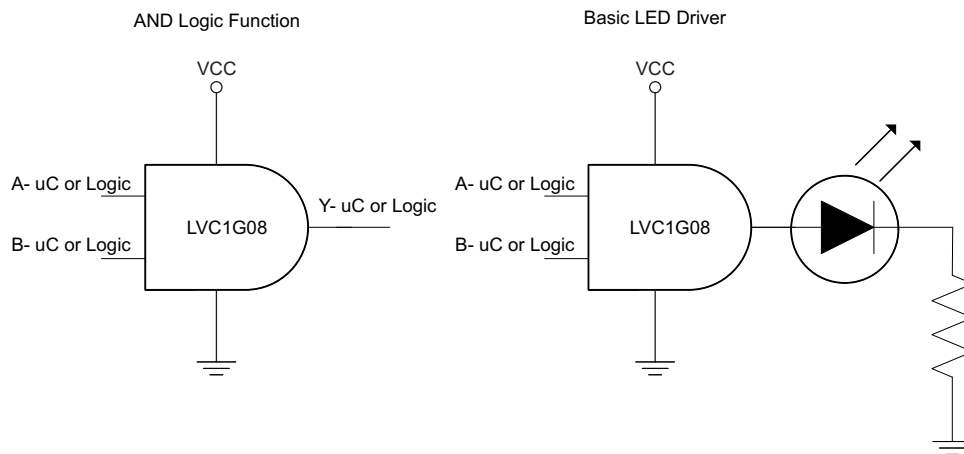


Figure 6. Typical Application Example

#### 9.2.1 Design Requirements

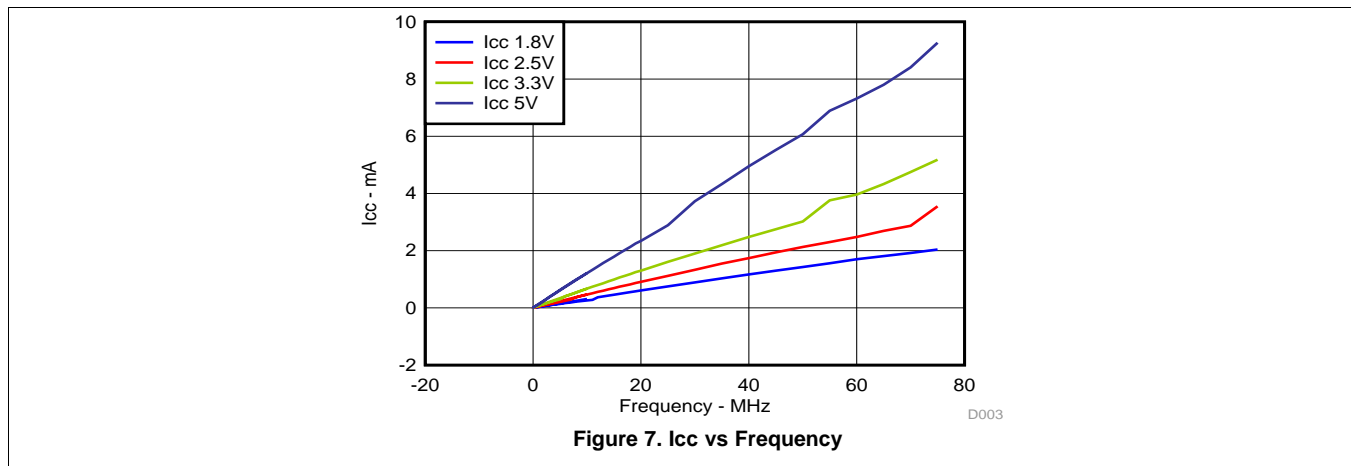
This device uses CMOS technology and has balanced output drive. Care should be taken to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads so routing and load conditions should be considered to prevent ringing.

#### 9.2.2 Detailed Design Procedure

1. Recommended Input Conditions
  - Rise time and fall time specs. See  $(\Delta t/\Delta V)$  in the [Recommended Operating Conditions](#) table.
  - Specified high and low levels. See  $(V_{IH}$  and  $V_{IL})$  in the [Recommended Operating Conditions](#) table.
  - Inputs are overvoltage tolerant allowing them to go as high as  $(V_I \text{ max})$  in the [Recommended Operating Conditions](#) table at any valid  $V_{CC}$ .
2. Recommend Output Conditions
  - Load currents should not exceed  $(I_O \text{ max})$  per output and should not exceed total current (continuous current through  $V_{CC}$  or GND) for the part. These limits are located in the [Absolute Maximum Ratings](#) table.
  - Outputs should not be pulled above  $V_{CC}$ .

## Typical Application (continued)

### 9.2.3 Application Curves



## 10 Power Supply Recommendations

The power supply can be any voltage between the min and max supply voltage rating located in the [Recommended Operating Conditions](#) table.

Each V<sub>CC</sub> pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1-μF capacitor is recommended and if there are multiple V<sub>CC</sub> pins then 0.01-μF or 0.022-μF capacitor is recommended for each power pin. It is ok to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1-μF and 1-μF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

## 11 Layout

### 11.1 Layout Guidelines

When using multiple bit logic devices inputs should not ever float. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. Specified below are the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to Gnd or V<sub>CC</sub> whichever make more sense or is more convenient.

### 11.2 Layout Example

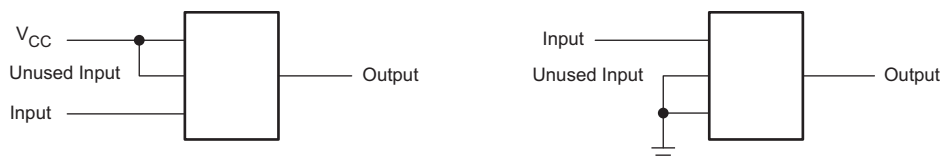


Figure 8. Layout Example

## 12 Device and Documentation Support

### 12.1 Trademarks

All trademarks are the property of their respective owners.

### 12.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### 12.3 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

## 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

## PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC1G08IDCKRQ1	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CEO	<a href="#">Samples</a>
SN74LVC1G08QDBVRQ1	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(33H5, C08O)	<a href="#">Samples</a>
SN74LVC1G08QDCKRQ1	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 125	(CEJ, CEO)	<a href="#">Samples</a>
SN74LVC1G08QDRYRQ1	ACTIVE	SON	DRY	6	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	EM	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSELETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

**Important Information and Disclaimer:**The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

**OTHER QUALIFIED VERSIONS OF SN74LVC1G08-Q1 :**

- Catalog : [SN74LVC1G08](#)
- Enhanced Product : [SN74LVC1G08-EP](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product
- Enhanced Product - Supports Defense, Aerospace and Medical Applications

**TAPE AND REEL INFORMATION**

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC1G08IDCKRQ1	SC70	DCK	5	3000	179.0	8.4	2.2	2.5	1.2	4.0	8.0	Q3
SN74LVC1G08QDBVRQ1	SOT-23	DBV	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1G08QDCKRQ1	SC70	DCK	5	3000	179.0	8.4	2.2	2.5	1.2	4.0	8.0	Q3
SN74LVC1G08QDCKRQ1	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1G08QDRYRQ1	SON	DRY	6	5000	180.0	9.5	1.2	1.65	0.7	4.0	8.0	Q1



**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC1G08IDCKRQ1	SC70	DCK	5	3000	200.0	183.0	25.0
SN74LVC1G08QDBVRQ1	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74LVC1G08QDCKRQ1	SC70	DCK	5	3000	200.0	183.0	25.0
SN74LVC1G08QDCKRQ1	SC70	DCK	5	3000	190.0	190.0	30.0
SN74LVC1G08QDRYRQ1	SON	DRY	6	5000	189.0	185.0	36.0



# EXAMPLE BOARD LAYOUT

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:15X



SOLDER MASK DETAILS

4214839/K 08/2024

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE:15X

4214839/K 08/2024

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

## GENERIC PACKAGE VIEW

**DRY 6**

**USON - 0.6 mm max height**

PLASTIC SMALL OUTLINE - NO LEAD



Images above are just a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.

4207181/G

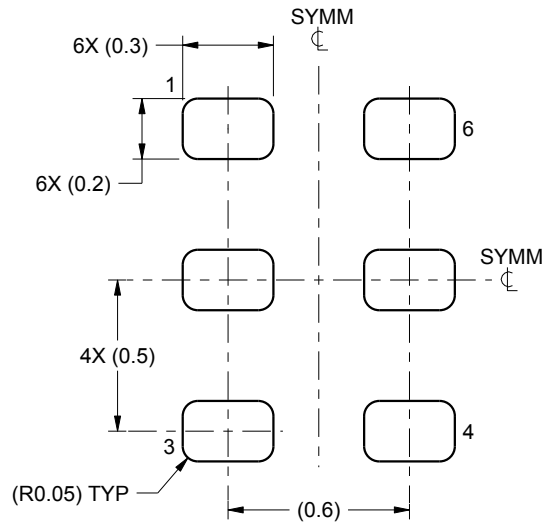


# EXAMPLE BOARD LAYOUT

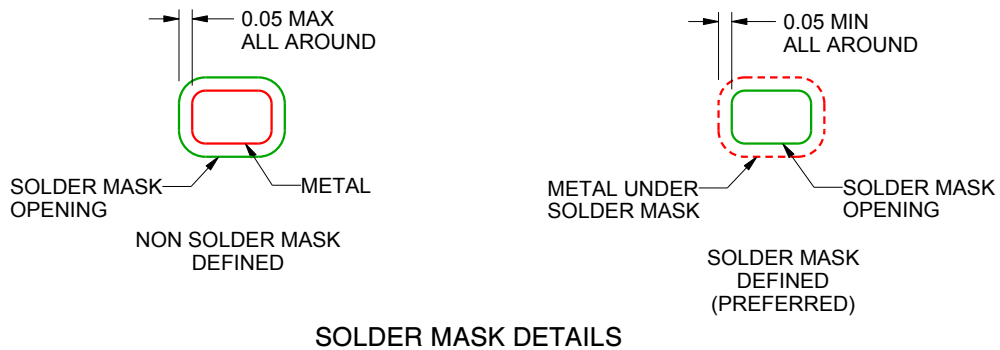
DRY0006B

USON - 0.55 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



LAND PATTERN EXAMPLE  
1:1 RATIO WITH PKG SOLDER PADS  
SCALE:40X



SOLDER MASK DETAILS

4222207/B 02/2016

NOTES: (continued)

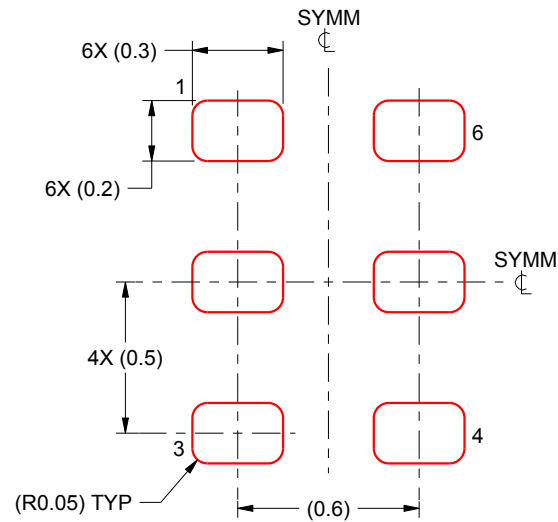
3. For more information, see QFN/SON PCB application report in literature No. SLUA271 ([www.ti.com/lit/sluea271](http://www.ti.com/lit/sluea271)).

# EXAMPLE STENCIL DESIGN

DRY0006B

USON - 0.55 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



SOLDER PASTE EXAMPLE  
BASED ON 0.075 - 0.1 mm THICK STENCIL  
SCALE:40X

4222207/B 02/2016

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



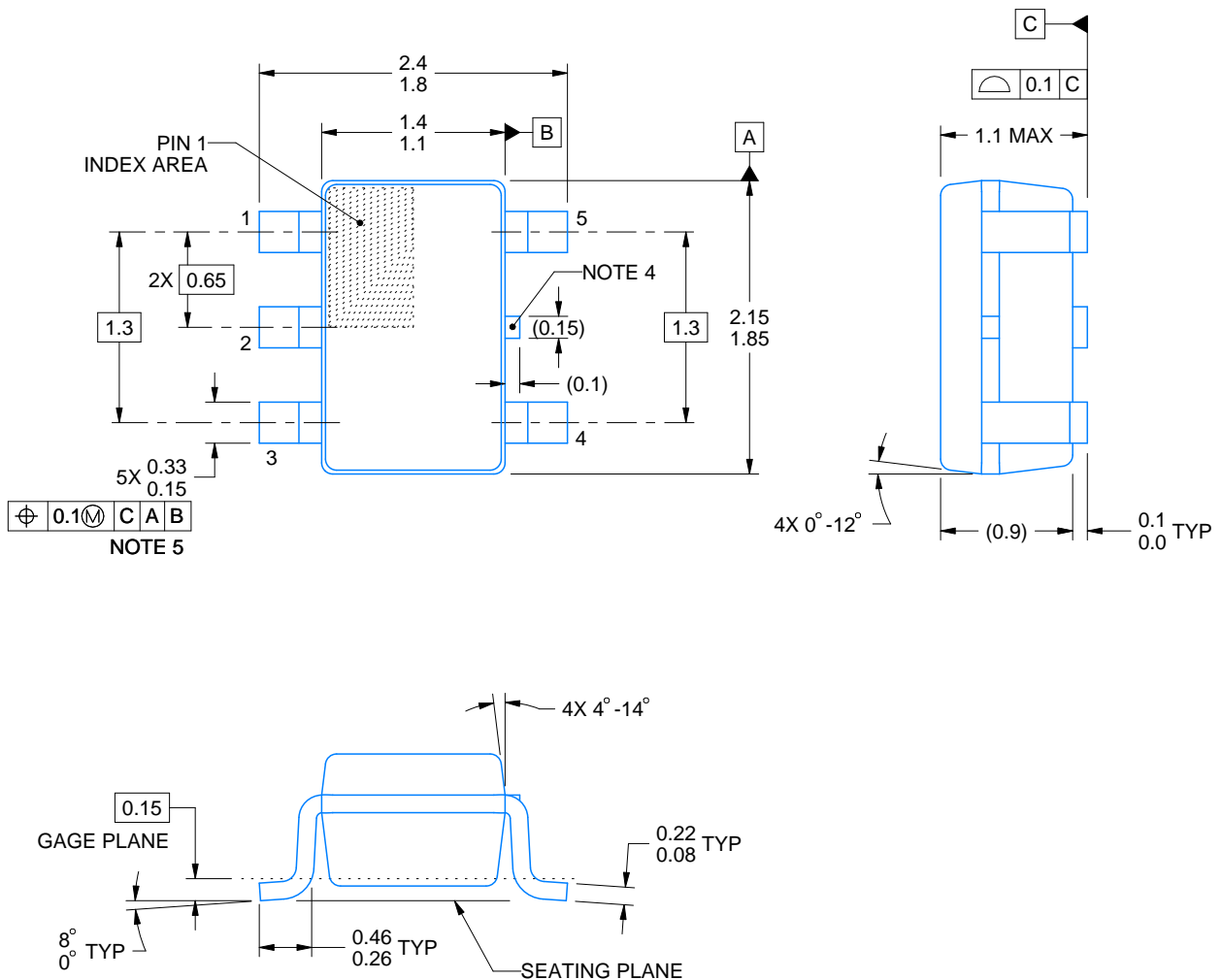


# PACKAGE OUTLINE

DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



4214834/F 08/2024

## NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-203.
4. Support pin may differ or may not be present.
5. Lead width does not comply with JEDEC.
6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side

# EXAMPLE BOARD LAYOUT

DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:18X



SOLDER MASK DETAILS

4214834/F 08/2024

NOTES: (continued)

- 7. Publication IPC-7351 may have alternate designs.
- 8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE  
BASED ON 0.125 THICK STENCIL  
SCALE: 18X

4214834/F 08/2024

NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
10. Board assembly site may have different recommendations for stencil design.

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